

Vishay Semiconductors

Hyperfast Rectifier, 4 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	4 A			
V _R	600 V			
V _F at I _F	1.2 V			
t _{rr} typ.	30 ns			
T _J max.	175 °C			
Package	SMB (DO-214AA)			
Circuit configuration	Single			

FEATURES

- Hyperfast recovery time, reduced Q_{rr} and soft recovery
- 175 °C maximum operating junction temperature
- ROHS COMPLIANT HALOGEN FREE
- For PFC CRM/CCM, snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: SMB (DO-214AA)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes the cathode end

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		600	V
Average rectified forward current	I _{F(AV)}	T _L = 76 °C ⁽¹⁾	4	۸
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C, 6 ms square pulse	55	^
Operating junction and storage temperatures	T _J , T _{Stq}		-55 to +175	°C

Note

(1) Mounted on PCB with minimum pad size

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-	
Conveyed welltone	V	I _F = 4 A	-	1.6	1.95	V
Forward voltage	V _F	I _F = 4 A, T _J = 150 °C	-	1.2	1.4	
Reverse leakage current	1_	V _R = V _R rated	-	-	3	
	IR	T _J = 150 °C, V _R = V _R rated	-	-	100	μA
Junction capacitance	C _T	V _R = 600 V	-	5.7	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
			$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		30	-	
		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	35	-	
Reverse recovery time t _{rr}	t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	35	ns
		T _J = 25 °C		-	22	-	
		T _J = 125 °C		-	37	-	
Dook room ourrent	ak recovery current I _{RRM} -	T _J = 25 °C	I _F = 4 A dI _F /dt = 200 A/μs	-	3.4	-	А
reak recovery current IRRM		T _J = 125 °C	$V_{R} = 390 \text{ V}$	-	5.2	-	_ A
Reverse recovery charge Q _{rr}	T _J = 25 °C		-	40	-	nC	
	T _J = 125 °C		-	103	-	i iiC	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J , T_{Stg}		-55	-	175	°C
Thermal resistance, junction to mount	R _{thJM} (1)		=	-	18	°C/W
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾		-	-	90	C/VV
Approximate Meight				0.1	•	g
Approximate Weight				0.003		OZ.
Marking device		Case style SMB (DO-214AA)		41	- 16	

Note

⁽¹⁾ Mounted on PCB with minimum pad size

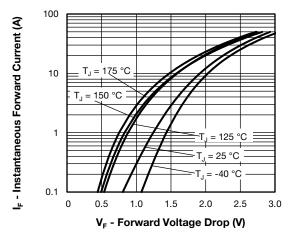


Fig. 1 - Typical Forward Voltage Drop Characteristics

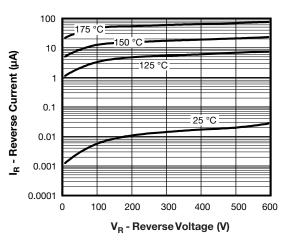


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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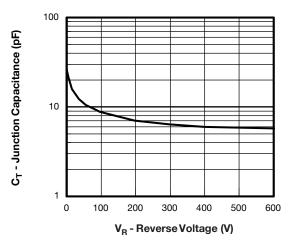


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

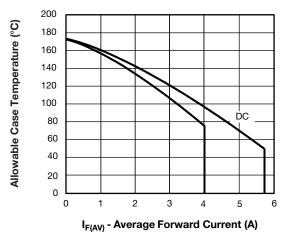


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

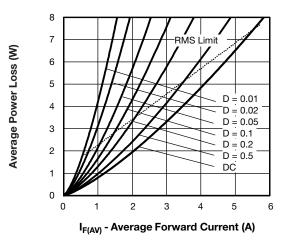


Fig. 5 - Forward Power Loss Characteristics

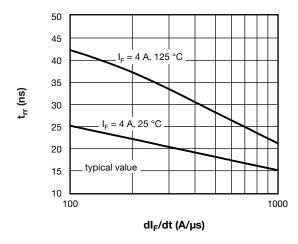


Fig. 6 - Typical Reverse Recovery vs. dI_F/dt

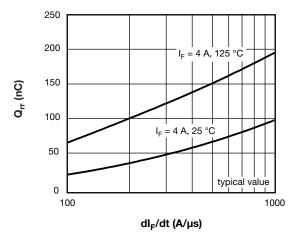
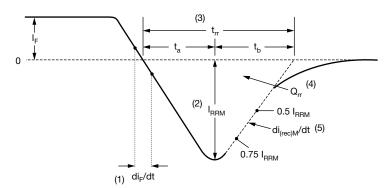


Fig. 7 - Typical Stored Charge vs. dl_F/dt

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{r}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

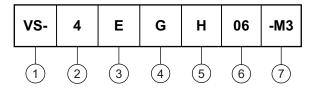
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (4 = 4 A)
- 3 Circuit configuration:

E = single diode

- G = SMB package

5 - Process type,

H = hyperfast recovery

Voltage code (06 = 600 V)

7 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION					
VS-4EGH06-M3/5BT	5BT	3200	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95401</u>				
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			

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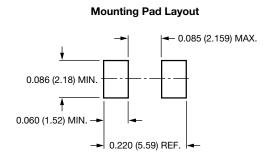


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SMB

DIMENSIONS in inches (millimeters)

0.086 (2.20) 0.077 (1.95) 0.180 (4.57) 0.160 (4.06) 0.096 (2.44) 0.084 (2.13) 0.0008 (0.2) 0.0008 (0.2) 0.0008 (0.2) 0.0008 (0.2) 0.0008 (0.2) 0.0008 (0.2) 0.0009 (0.2005 (5.21)



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